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P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
- 20	19 at V _{GS} = - 4.5 V	- 8.5	15.5 nC			
- 20	24.8 at V _{GS} = - 2.5 V	- 6.5	15.5 110			

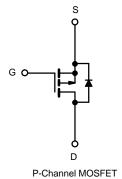
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS tested
- · Low Gate Charge



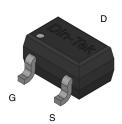
APPLICATIONS

- · Load Switches
- DC/DC Converters



SOT-23-3L Pin Configuration

Top View



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	- 20	V			
Gate-Source Voltage	V _{GS}	± 12	V			
Continuous Drain Current /T = 150° C\a	T _A = 25 °C	1	- 8.5			
Continuous Drain Current (T _J = 150° C) ^a	T _A = 100 °C	I _D	- 6.3	А		
Pulsed Drain Current ^b	I _{DM}	- 34				
Mayimum Dawar Dissipations	T _A = 25 °C	В	2.8	10/		
Maximum Power Dissipation ^c	T _A = 100 °C	P _D	1.12	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Case (Drain)	R _{thJA}	44.6	°C/W		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS} $V_{GS} = 0 \text{ V}, I_D = -250 \mu A$		- 20	-	-	.,	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.45	-	- 1	V	
Gate-Body Leakage	I _{GSS}			-	± 100	nA	
7 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	-	-	- 1	- 1 - 10 μΑ	
Zero Gate Voltage Drain Current		V _{DS} =-16V, V _{GS} = 0 V, T _J = 55 °C	-	-	- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥– 5 V, V _{GS} = - 10 V	- 8.5	-	-	Α	
Drain-Source On-State Resistance a	D	V _{GS} = - 4.5 V, I _D = - 5 A	-	19	25	C	
Diam-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 5 A	-	24.8	33	mΩ	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 5 A	-	7.8	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	1350	-	pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 10 V, f = 1 MHz	-	155	-		
Reverse Transfer Capacitance	C _{rss}		-	120	-		
Total Gate Charge ^c	Qg		-	15.5	-	nC	
Gate-Source Charge ^c	Q_{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 5 A	-	1.9	-		
Gate-Drain Charge ^c	Q_{gd}		-	3.2	-		
Gate Resistance	R _g	f = 1 MHz	-	11	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	5.5	-		
Rise Time ^c	t _r	$V_{DD} = -10 \text{ V}, R_{q} = 3 \Omega,$	-	11	-		
Turn-Off Delay Time ^c	t _{d(off)}	In = - 5 A , Vgs = - 4.5 V	-	20	-	ns	
Fall Time ^c	t _f		-	6	-		
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _A = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _A = 25 °C	-	-	- 8.5	Α	
Pulsed Current	I _{SM}		-	-	- 34	Α	
Forward Voltage ^a	V_{SD}	I _F = - 1 A, V _{GS} = 0 V	-	-	-1.2	V	
Reverse Recovery Time	t _{rr}	I _F = - 5 A, di/dt = 100 A/µs	-	15	-	ns	
Reverse Recovery Charge	Q_{rr}	rr - 375, αναί - 10077 μ3		8	-	nC	

Notes

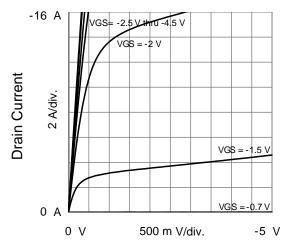
- a. Pulse test; pulse width \leq 400 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not su bject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.

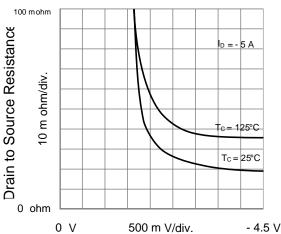


CHANNEL TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

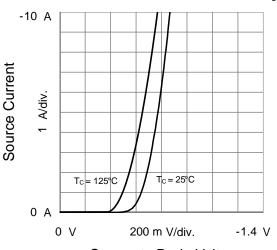
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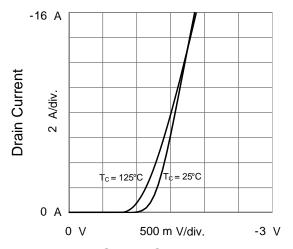
Drain to Source Voltage Output Characteristics



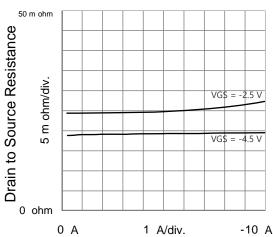
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



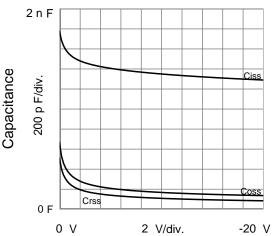
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



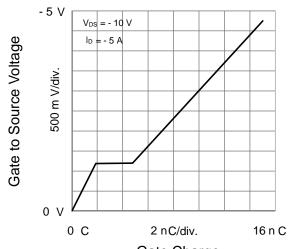
Drain Current
Drain to Source Resistance vs. Drain Current



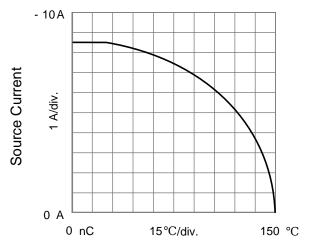
Drain to Source Voltage Capacitances

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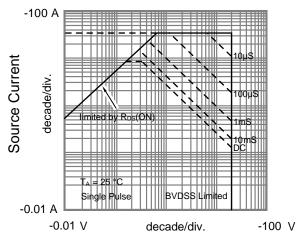
CHANNEL TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)



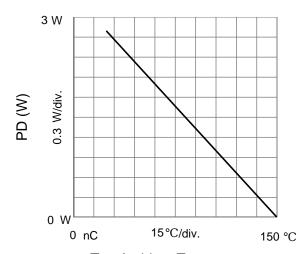
Gate Charge
Gate to Source Voltage vs. GateCharge



T_A - Ambient Temperature Current Derating

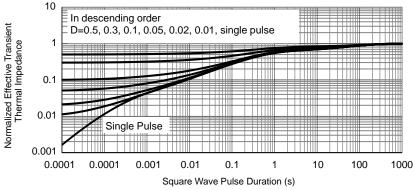


Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_A - Ambient Temperature

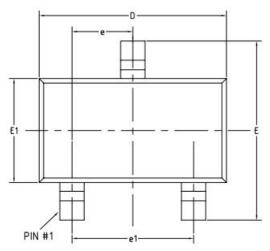
Power Derating

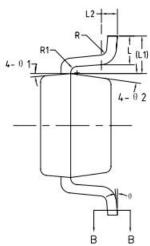


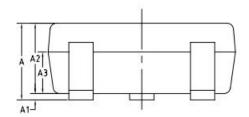
Normalized Thermal Transient Impedance, Junction-to-Ambient

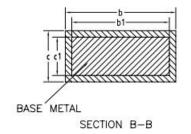


SOT-23-3L PACKAGE OUTLINE









COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	
А	-	-	1.50	
A1	0.00	-	0.18	
A2	0.85	1.10	1.35	
А3	0.58	0.65	0.72	
b	0.23	-	0.53	
b1	0.20	0.40	0.50	
С	0.09	-	0.22	
c1	0.08	0.13	0.21	
D	2.78	2.95	3.10	
Е	2.58	2.80	3.03	
E1	1.55	1.65	1.78	
е	0.83	0.95	1.07	
e1	1.78	1.90	2.02	
L	0.28	0.45	0.62	
L1	0.59REF			
L2	0.25BSC			
R	0.04	-	-	
R1	0.04	-	0.21	
θ	0°	-	8°	
θ1	8°	10°	12°	
θ2	8°	10°	12°	





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